

SANYO Semiconductors DATA SHEET

DATA OHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

5LP01S — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Ultrahigh-speed switching
- · 2.5V drive

Specifications

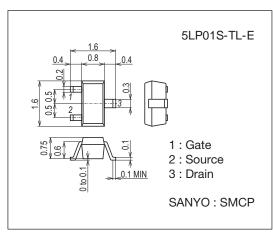
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-50	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-0.07	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-0.28	Α
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	$^{\circ}$
Storage Temperature	Tstg		-55 to +150	C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Package Dimensions

unit : mm (typ) 7027-004

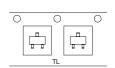


Product & Package Information

• Package : SMCP

• JEITA, JEDEC : SC-75, SOT-416 • Minimum Packing Quantity : 3,000 pcs./reel

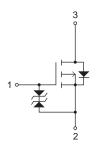
Packing Type: TL



Marking



Electrical Connection



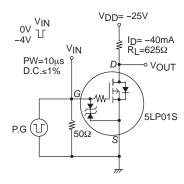
^{*} Machine Model

5LP01S

Electrical Characteristics at Ta=25°C

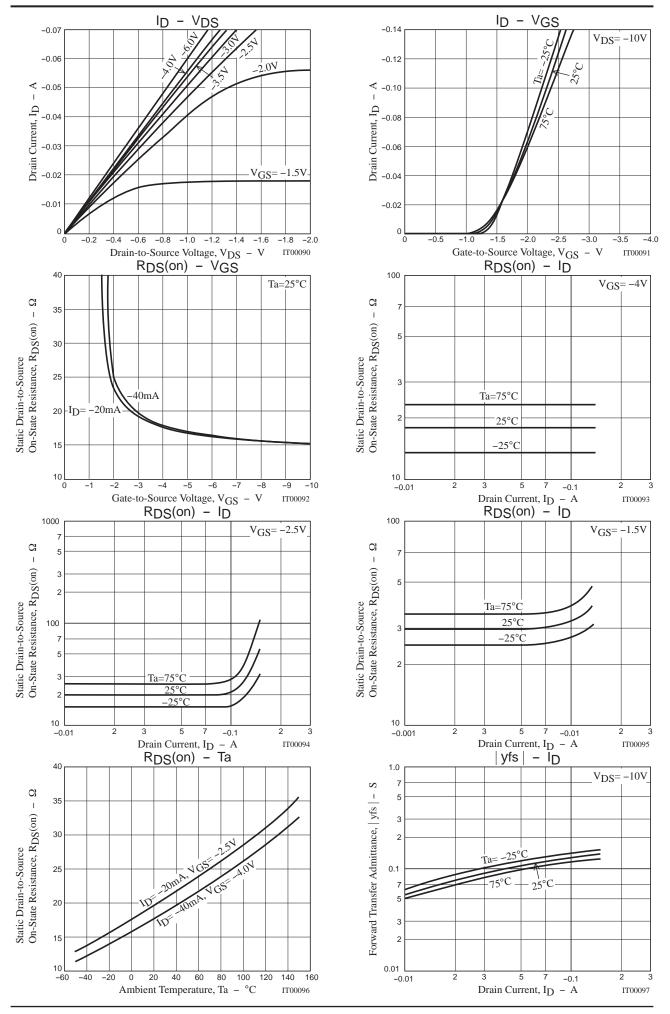
Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID= -1mA, VGS=0V	-50			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = -50V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} = -10V, I _D = -100μA	-0.4		-1.4	V	
Forward Transfer Admittance	yfs	V _{DS} = -10V, I _D = -40mA	70	100		mS	
Static Drain-to-Source On-State Resistance	RDS(on)1	I _D = -40mA, V _G S= -4V		18	23	Ω	
	R _{DS} (on)2	I _D = -20mA, V _G S= -2.5V		20	28	Ω	
	R _{DS} (on)3	I _D = -5mA, V _G S= -1.5V		30	60	Ω	
Input Capacitance	Ciss			7.4		рF	
Output Capacitance	Coss	V _{DS} = -10V, f=1MHz		4.2		pF	
Reverse Transfer Capacitance	Crss			1.3		pF	
Turn-ON Delay Time	t _d (on)			20		ns	
Rise Time	t _r	On an ariffed Total Circuit		35		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		160		ns	
Fall Time	tf			150		ns	
Total Gate Charge	Qg			1.40		nC	
Gate-to-Source Charge	Qgs	V _{DS} = -10V, V _{GS} = -10V, I _D = -70mA		0.16		nC	
Gate-to-Drain "Miller" Charge	Qgd			0.23		nC	
Diode Forward Voltage	V _{SD}	I _S = -70mA, V _{GS} =0V		-0.85	-1.2	V	

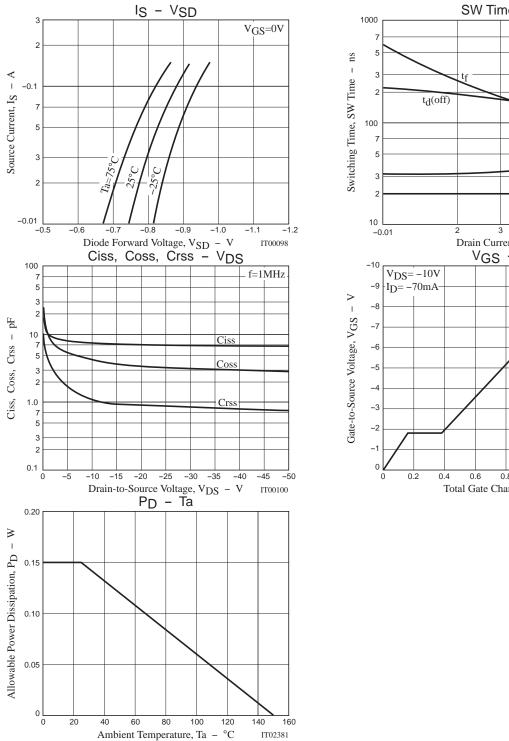
Switching Time Test Circuit

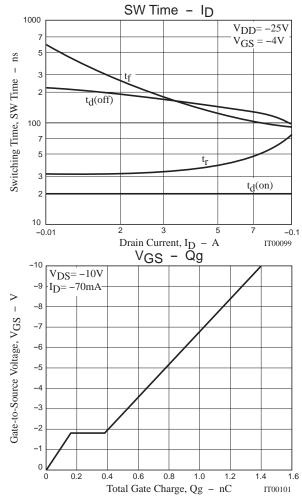


Ordering Information

Device	Device Package		memo	
5LP01S-TL-E	SMCP	3,000pcs./reel	Pb Free	





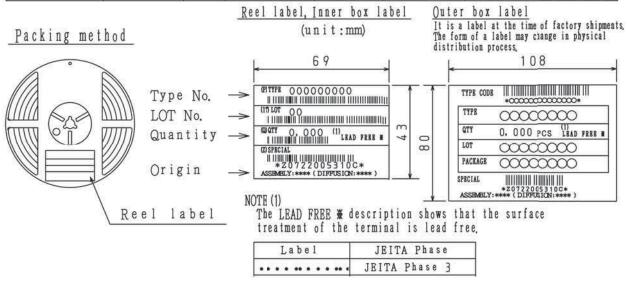


Embossed Taping Specification

5LP01S-TL-E

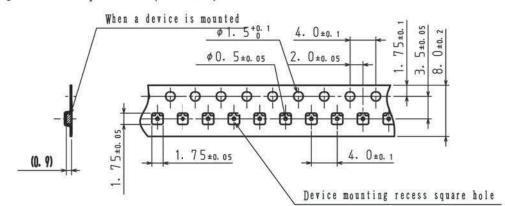
1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
SMCP	SMCP	3, 000	15, 000	90,000	5 reels contained Dimensions:mm (external)	6 inner boxes contained Dimensions:mm (external)	
					183×72×185	440×195×210	

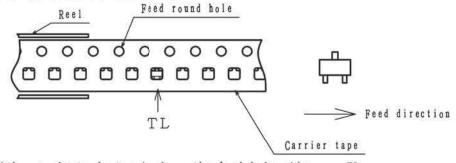


2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



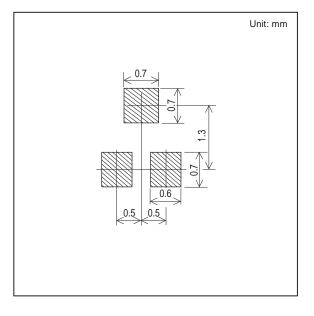
Those with one electrode terminal on the feed hole side·····TL

Outline Drawing

5LP01S-TL-E

| Mass (g) | Unit | 0.003 | mm | 1.546.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.4 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1 | 0.846.1

Land Pattern Example



Note on usage: Since the 5LP01S is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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